

RF POWER FET TRANSISTOR

DESCRIPTION:

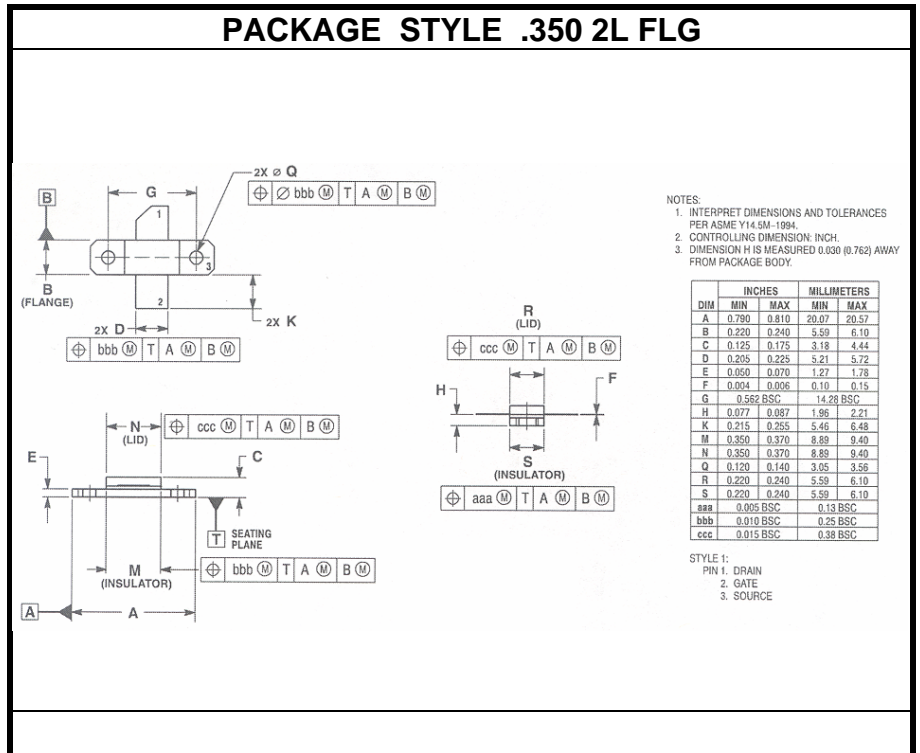
The ASI MRF182 is an RF power field effect transistor, N-Channel Enhancement-Mode lateral MOSFET.

FEATURES INCLUDE:

- Broadband performance from HF to 1 GHz
- **Omnigold™** Metalization System
- High Gain, Rugged device.

MAXIMUM RATINGS

V_{DSS}	65 V
V_{GS}	±20 V
P_D	74 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.75 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I _D = 1.0 μA			65			V
I_{DSS}	V _{DS} = 28 V	V _{GS} = 0 V				1.0	μA
I_{GSS}	V _{DS} = 0 V	V _{GS} = 20 V				1.0	μA
V_{GS(th)}	V _{DS} = 10 V	I _D = 100 μA		2.0	3.0	4.0	V
V_{GS(Q)}	V _{DS} = 28 V	I _D = 50 mA		3.0	4.0	5.0	V
V_{DS(on)}	V _{GS} = 10 V	I _D = 3.0 A			0.9	1.2	V
g_{fs}	V _{DS} = 10 V	I _D = 3.0 A		1.6	1.8		S
C_{iss}	V _{DS} = 28 V	V _{GS} = 0 V	f = 1.0 MHz		56		pF
C_{oss}				28			
C_{rss}				2.5			
G_{PS}	V _{DD} = 28 V	P _{OUT} = 30 W	f = 945 MHz	11	14		dB
η	I _{DQ} = 50 mA			50	58		%